

L660N-04

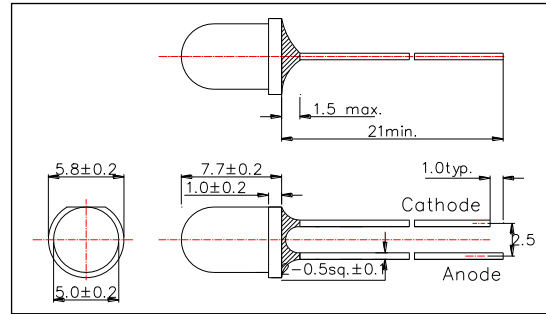
For Plant Growth / Photo Synthetically Active Radiation Use

L660N-04 is an AlGaInP LED mounted on a lead frame with a clear epoxy resin. This is designed for the highest Po and damp proof. On forward bias, it emits a band of visible light that peaks 660nm.

<Specifications>

1. Product Name: Red LED Lamp
2. Type Number: L660N-04
3. Chip:
 - Chip material: AlGaInP
 - Peak Wavelength: 660nm type
4. Package
 - Type: Φ5mm Clear Molding
 - Resin Material: Epoxy Resin
 - Lead Frame: Soldered(Lead Free)

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	120	mW
Forward Current	IF	50	mA
Pulse Forward Current*	IFP	200	mA
Reverse Voltage	VR	5	V
Operating Temperature	TOPR	-30 ~ +80	°C
Storage Temperature	TSTG	-40 ~ +100	°C
Soldering Temperature***	TSOL	265	°C

* Duty=1% and Pulse Width=10us.

** Soldering condition must be completed within 3 second at 265 °C.

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=20mA		2.1	2.3	V
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power*	PO	IF=20mA	8	15		mW
Radiant Intensity	IE	IF=20mA		11		mW/sr
Brightness**	IV	IF=20mA		700		mcd
Peak Wavelength	λP	IF=20mA	650	660	670	nm
Half Width	Δλ	IF=20mA		18		nm
Viewing Half Angle	θ1/2	IF=20mA		±28		deg

* Measured by Photodyne #500

** Measured by Tektronix J-16

